

# Enhancement Mode N-Channel Power MOSFET

## Features

- ◆ Low  $R_{DS(on)}$  & FOM
- ◆ Extremely low switching loss
- ◆ Excellent stability and uniformity
- ◆ Easy to drive
- ◆ EMI and performance balanced

## Applications

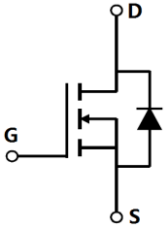
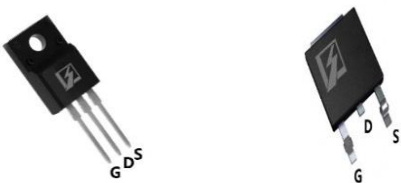

- ◆ Lighting
- ◆ Hard switching PWM
- ◆ Server power supply
- ◆ Charger

## ■ General Description

OSG65R580xEF use advanced GreenMOSTM technology to provide low  $R_{DS(ON)}$ , low gate charge, fast switching and excellent avalanche characteristics. This device is suitable for active power factor correction and switching mode power supply applications.

◆ $V_{DS, min@Tjmax}$	700 V
◆ $I_{D, pulse}$	24 A
◆ $R_{DS(ON), max @ V_{GS}=10 V}$	580 mΩ
◆ $Q_g$	12.4 nC

## ■ Schematic and Package Information

<b>Schematic Diagram</b> 	<b>PIN ASSIGNMENT TOP VIEW</b>  <b>TO220F</b> <b>OSG65R580FEF</b>	 <b>TO252</b> <b>OSG65R580DEF</b>
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## ■ Absolute Maximum Ratings at $T_j=25^{\circ}C$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain source voltage	$V_{DS}$	650	V
Gate source voltage	$V_{GS}$	±30	V
Continuous drain current <sup>1)</sup> , $T_C=25^{\circ}C$	$I_D$	8	A
Continuous drain current <sup>1)</sup> , $T_C=100^{\circ}C$		5	
Pulsed drain current <sup>2)</sup> , $T_C=25^{\circ}C$	$I_{D, pulse}$	24	A
Power dissipation <sup>3)</sup> for TO252, $T_C=25^{\circ}C$	$P_D$	63	W
Power dissipation <sup>3)</sup> for TO220F, $T_C=25^{\circ}C$		28	
Single pulsed avalanche energy <sup>5)</sup>	$E_{AS}$	150	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0...480 V$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0...480 V, I_{SD} \leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	$T_{stg}, T_j$	-55 to 150	°C

## ■ Thermal Characteristics

Parameter	Symbol	Value		Unit
		TO252	TO220F	
Thermal resistance, junction-case	$R_{\theta JC}$	2	4.5	°C/W
Thermal resistance, junction-ambient <sup>4)</sup>	$R_{\theta JA}$	62	62.5	°C/W

## ■ Electrical Characteristics at $T_j=25\text{ }^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	$BV_{DSS}$	650			V	$V_{GS}=0\text{ V}$ , $I_D=250\text{ }\mu\text{A}$
		700	750			$V_{GS}=0\text{ V}$ , $I_D=250\text{ }\mu\text{A}$ , $T_j=150\text{ }^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.0		4.0	V	$V_{DS}=V_{GS}$ , $I_D=250\text{ }\mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.48	0.58	$\Omega$	$V_{GS}=10\text{ V}$ , $I_D=4\text{ A}$
			1.27			$V_{GS}=10\text{ V}$ , $I_D=4\text{ A}$ , $T_j=150\text{ }^{\circ}\text{C}$
Gate-source leakage current	$I_{GSS}$			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS}=650\text{ V}$ , $V_{GS}=0\text{ V}$

## ■ Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	$C_{iss}$		587		pF	$V_{GS}=0\text{ V}$ , $V_{DS}=50\text{ V}$ , $f=1\text{ MHz}$
Output capacitance	$C_{oss}$		42.1		pF	
Reverse transfer capacitance	$C_{rss}$		1.8		pF	
Turn-on delay time	$t_{d(on)}$		22.4		ns	$V_{GS}=10\text{ V}$ , $V_{DS}=400\text{ V}$ , $R_G=10\text{ }\Omega$ , $I_D=8\text{ A}$
Rise time	$t_r$		16.5		ns	
Turn-off delay time	$t_{d(off)}$		33.4		ns	
Fall time	$t_f$		5.1		ns	

## ■ Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	$Q_g$		12.4		nC	$I_D=8\text{ A}$ , $V_{DS}=400\text{ V}$ , $V_{GS}=10\text{ V}$
Gate-source charge	$Q_{gs}$		3.2		nC	
Gate-drain charge	$Q_{gd}$		5.0		nC	
Gate plateau voltage	$V_{\text{plateau}}$		6.0		V	

## ■ Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward current <sup>2)</sup>	$I_S$			8	A	$V_{GS}<V_{th}$
Pulsed source current	$I_{SP}$			24		
Diode forward voltage	$V_{SD}$			1.2	V	$I_S=8\text{ A}$ , $V_{GS}=0\text{ V}$
Reverse recovery time	$t_{rr}$		272.2		ns	$V_R=400\text{ V}$ , $I_S=8\text{ A}$ , $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	$Q_{rr}$		2.5		$\mu\text{C}$	
Peak reverse recovery current	$I_{rrm}$		20.7		A	

## ■ Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3)  $P_d$  is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with  $T_a=25\text{ }^\circ\text{C}$ .
- 5)  $V_{DD}=50\text{ V}$ ,  $R_G=25\text{ }\Omega$ ,  $L=10.8\text{ mH}$ , starting  $T_j=25\text{ }^\circ\text{C}$ .

■ **Electrical Characteristics Diagrams**

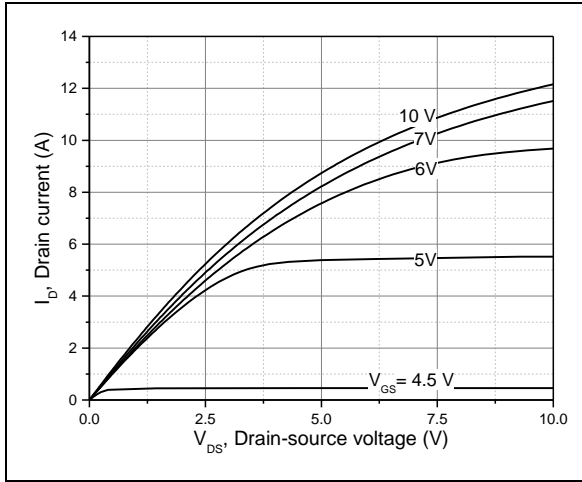


Figure 1, Typ. output characteristics

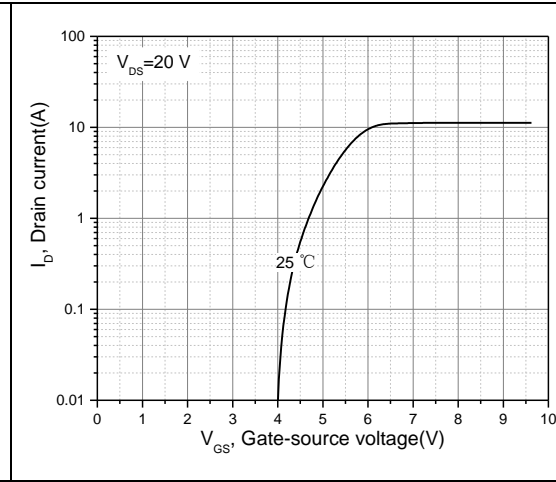


Figure 2, Typ. transfer characteristics

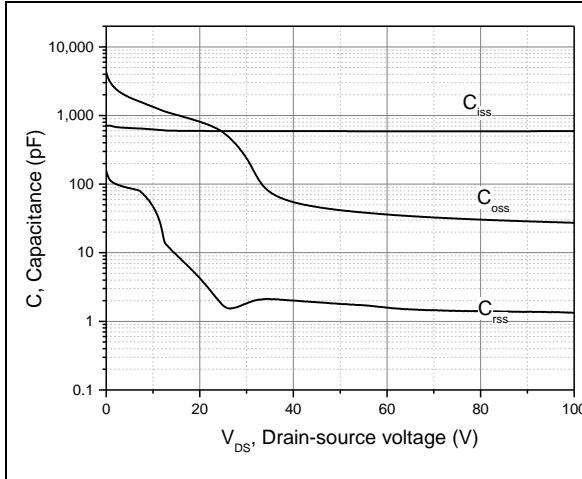


Figure 3, Typ. capacitances

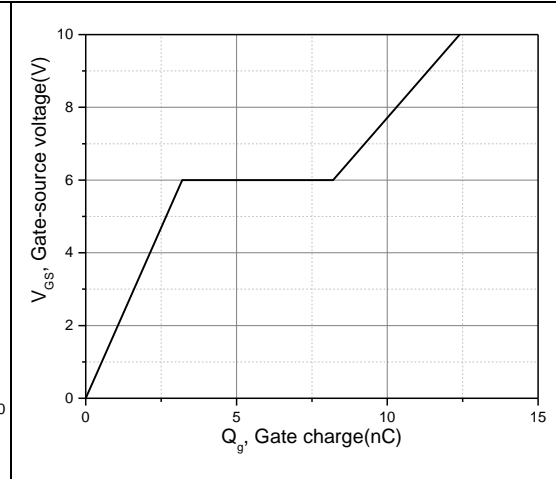


Figure 4, Typ. gate charge

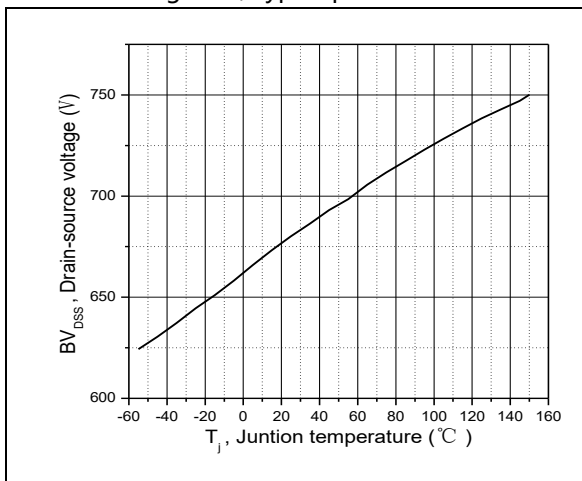


Figure 5, Drain-source breakdown voltage

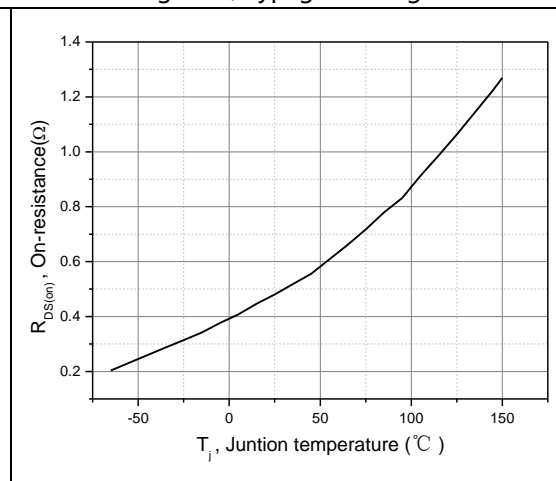


Figure 6, Drain-source on-state resistance

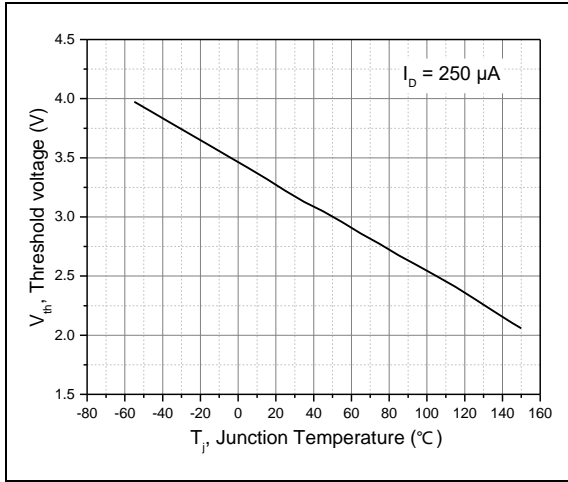


Figure 7, Threshold voltage

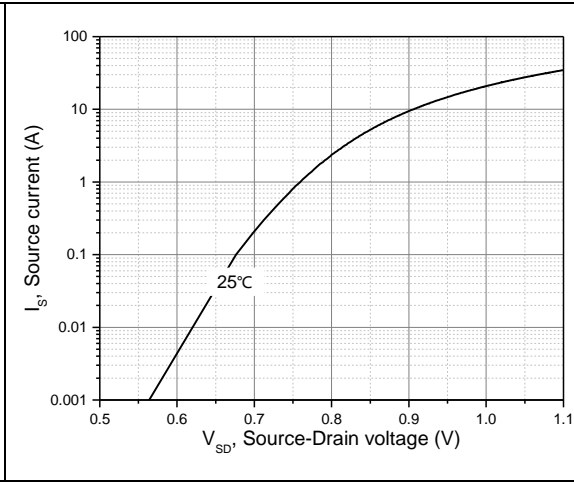


Figure 8, Forward characteristic of body diode

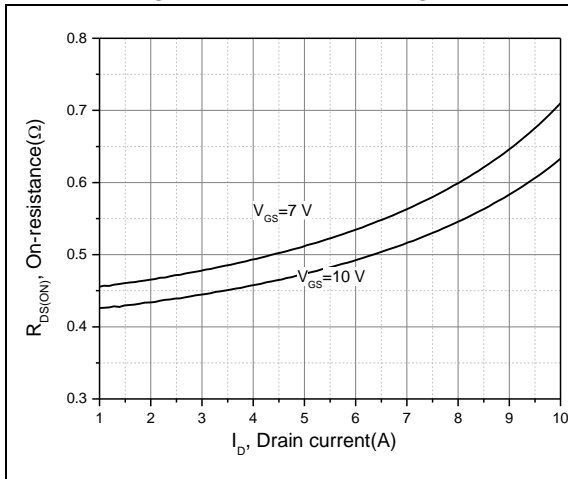


Figure 9, Drain-source on-state resistance

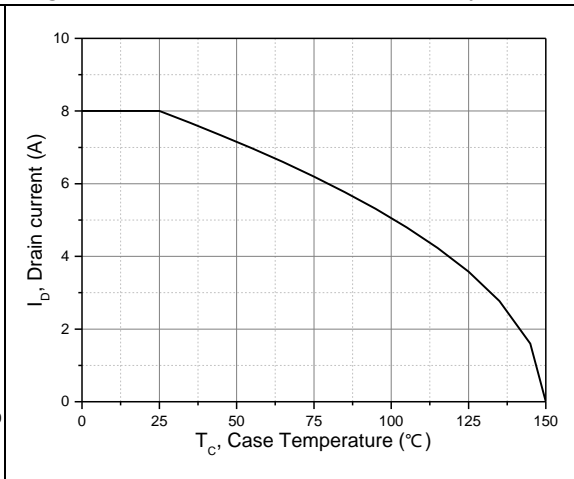


Figure 10, Drain current

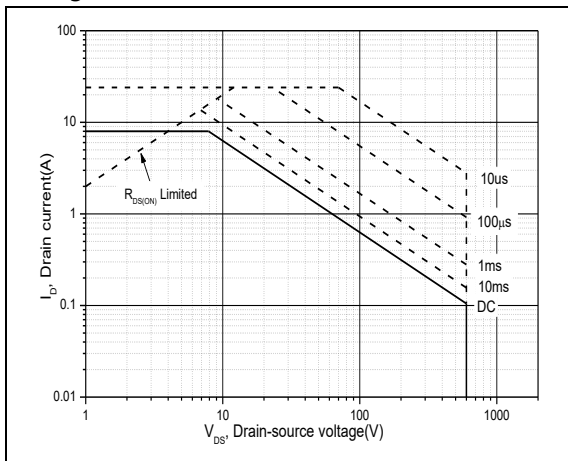


Figure 11, Safe operation area for TO252  
 $T_C = 25\text{ }^\circ\text{C}$

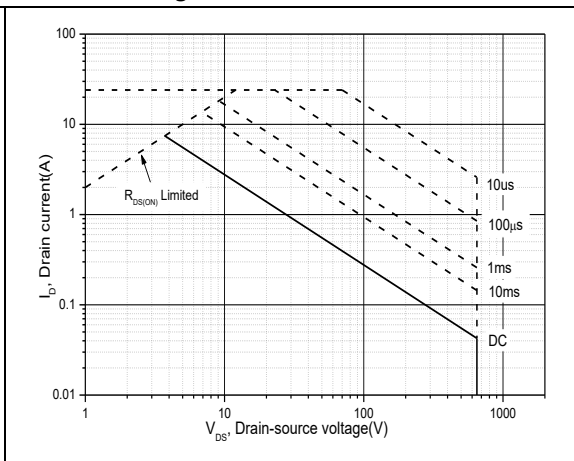


Figure 12, Safe operation area for TO220F  
 $T_C = 25\text{ }^\circ\text{C}$

■ Test circuits and waveforms

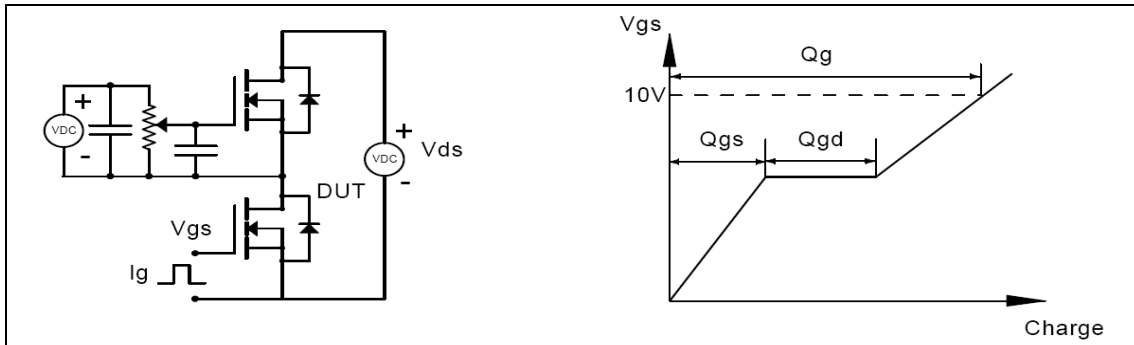


Figure 1, Gate charge test circuit & waveform

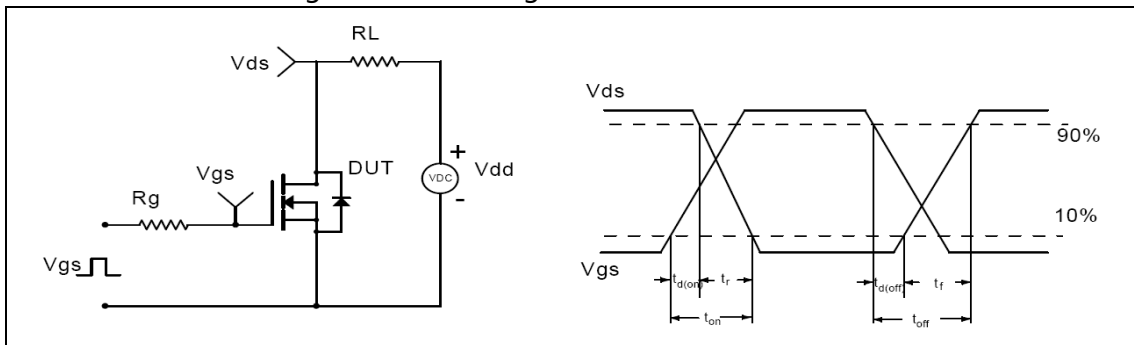


Figure 2, Switching time test circuit & waveforms

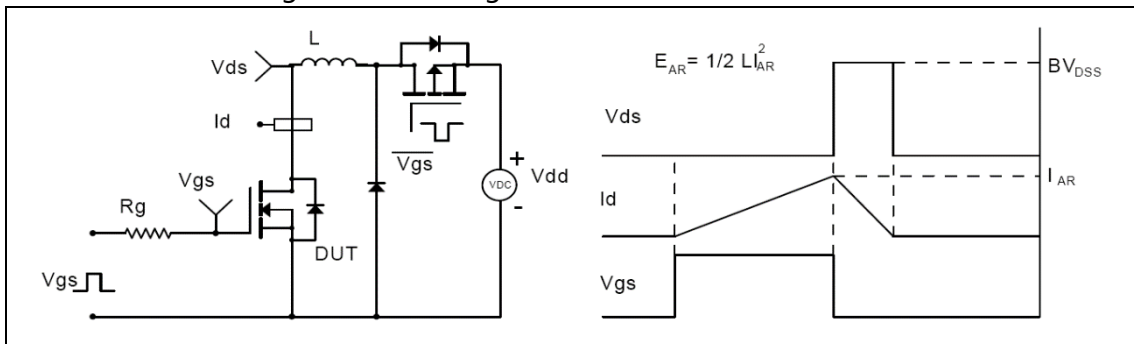


Figure 3, Unclamped inductive switching (UIS) test circuit & waveforms

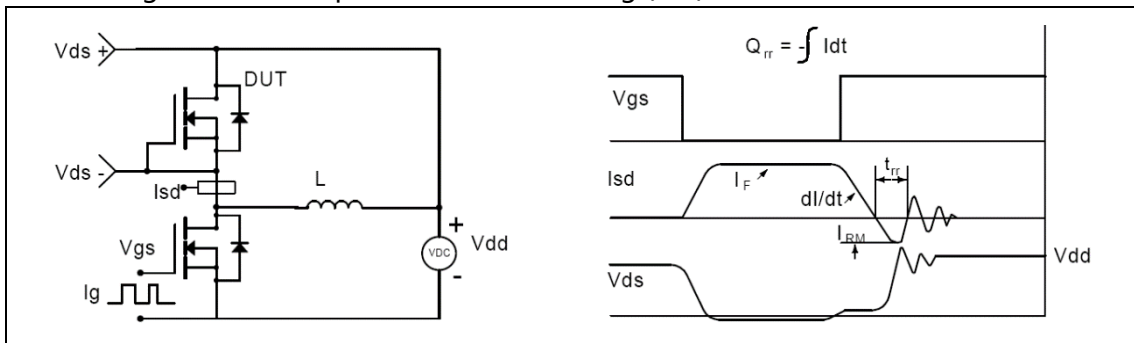
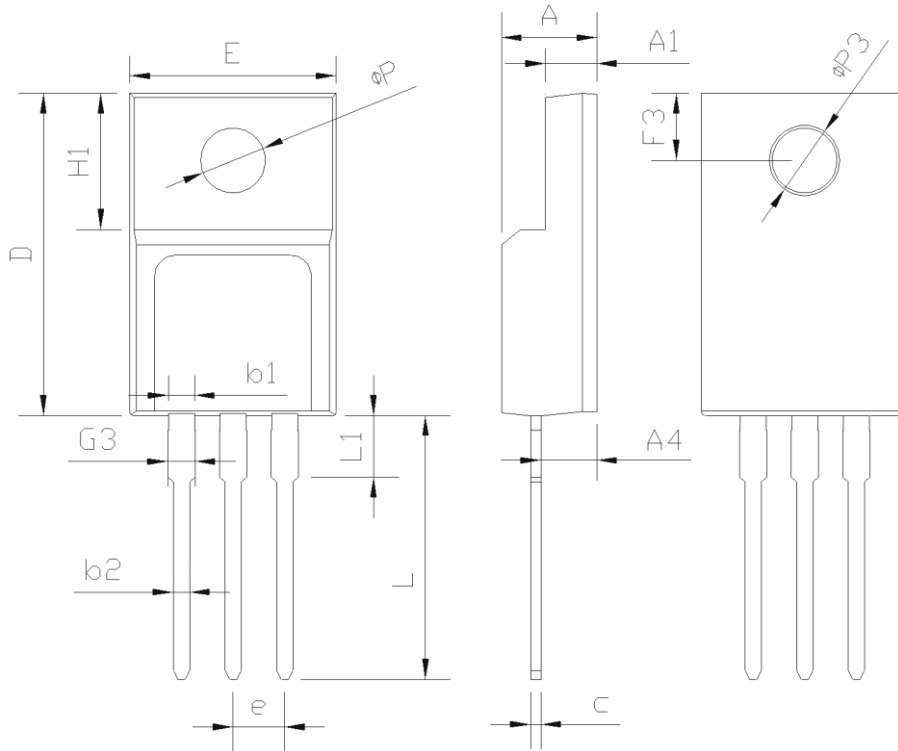


Figure 4, Diode reverse recovery test circuit & waveforms

**■ Package Information**

Figure1, TO220F package outline dimension

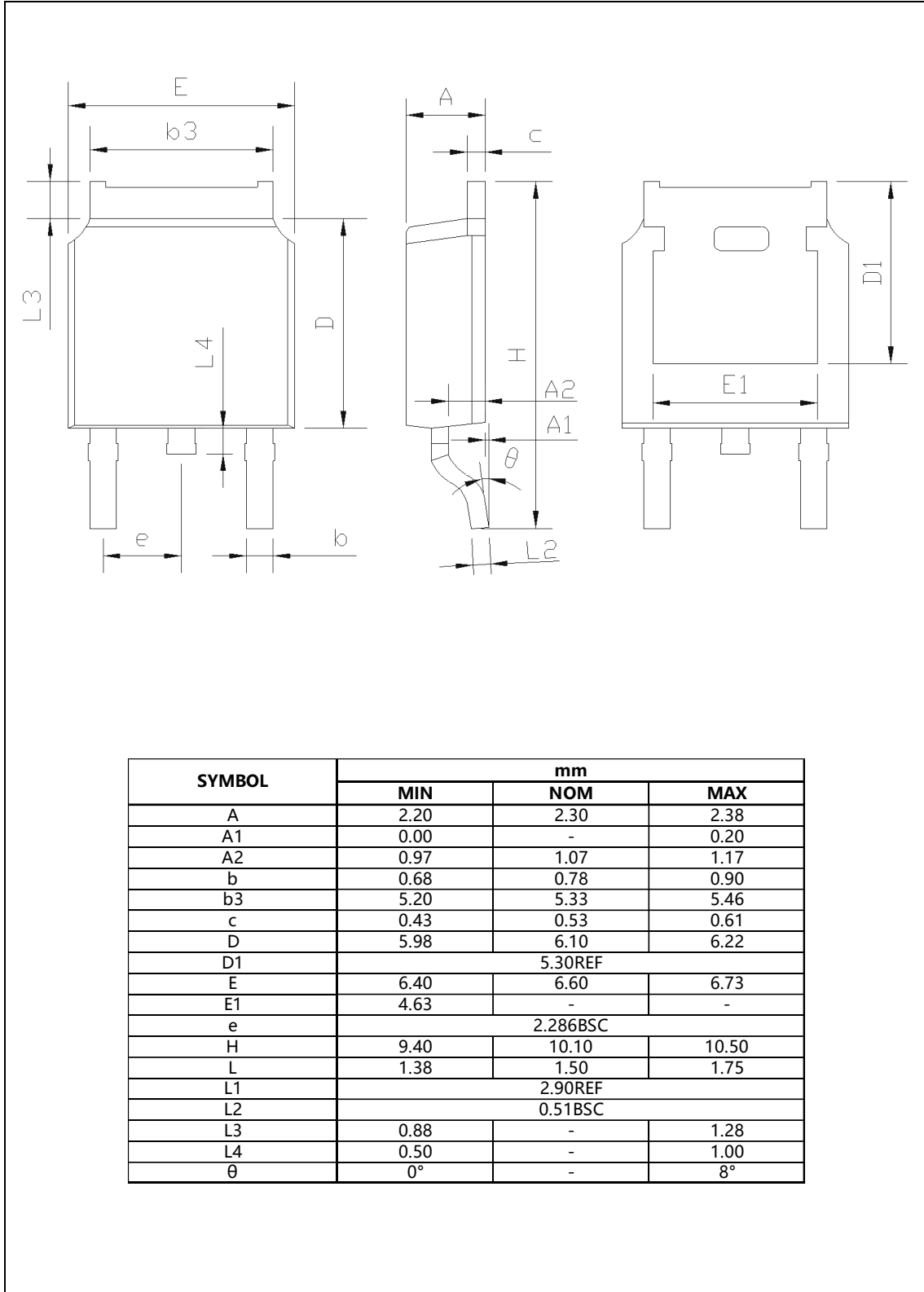


SYMBOL	mm		
	MIN	NOM	MAX
E	9.96	10.16	10.36
A	4.50	4.70	4.90
A1	2.34	2.54	2.74
A2	0.30	0.45	0.60
A4	2.56	2.76	2.96
c	0.40	0.50	0.65
c1	1.20	1.30	1.35
D	15.57	15.87	16.17
H1	6.70REF		
e	2.54BSC		
L	12.68	12.98	13.28
L1	2.88	3.03	3.18
ΦP	3.03	3.18	3.38
ΦP3	3.15	3.45	3.65
F3	3.15	3.30	3.45
G3	1.25	1.35	1.55
b1	1.18	1.28	1.43
b2	0.70	0.80	0.95



**■ Package Information**

Figure2, TO252 package outline dimension



## ■ Ordering Information

Package	Units/Tube	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO220F	50	20	1000	6	6000

Package	Units/Tape	Tubes/Inner Box	Units/Inner Box	Inner Box/Carton Box	Units/Carton Box
TO252	2500	2	5000	5	25000

## ■ Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSG65R580FEF	TO220F	yes	yes	yes
OSG65R580DEF	TO252	yes	yes	yes